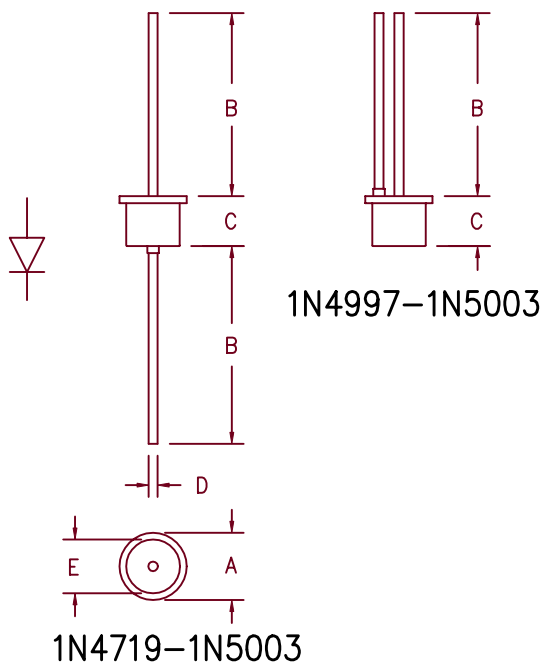


# Silicon Rectifiers

## 1N4719–1N4725, 1N4997–1N5003



Dim.	Inches		Millimeter		Notes
	Minimum	Maximum	Minimum	Maximum	
A	---	.450	---	11.43	Dia.
B	.980	---	24.89	---	
C	---	.300	---	7.62	
D	.046	.056	1.17	1.42	Dia.
E	---	.350	---	8.89	Dia.

Microsemi Catalog Number	Peak Reverse Voltage
1N4719, 1N4997	50V
1N4720, 1N4998	100V
1N4721, 1N4999	200V
1N4722, 1N5000	400V
1N4723, 1N5001	600V
1N4724, 1N5002	800V
1N4725, 1N5003	1000V

- High Surge Capability
- 175°C Junction Temperature
- VRRM 50 to 1000 Volts
- 3 Amp Current Rating
- Hermetically Sealed

Electrical Characteristics		
Average forward current	IF(AV) 3.0 Amps	TA = 119°C, Square wave, RθJL = 12°C/W, L = 1/4"
Maximum surge current	IFSM 300 Amps	8.3ms, half sine, TJ = 175°C
Max peak forward voltage	VFM 1.0 Volts	IFM = 3.0A: TJ = 25°C*
Max peak reverse current	IRM 25 μA	VRRM, TJ = 25°C
*Pulse test: Pulse width 300 μsec, Duty cycle 2%		

Thermal and Mechanical Characteristics		
Storage temperature range	TSTG	-65°C to 175°C
Operating junction temp range	TJ	-65°C to 175°C
Maximum thermal resistance	L = 1/4" RθJL	12°C/W Junction to Lead
Weight		.08 ounces (2.3 grams) typical

11-13-00 Rev. 1

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Figure 1  
Typical Forward Characteristics

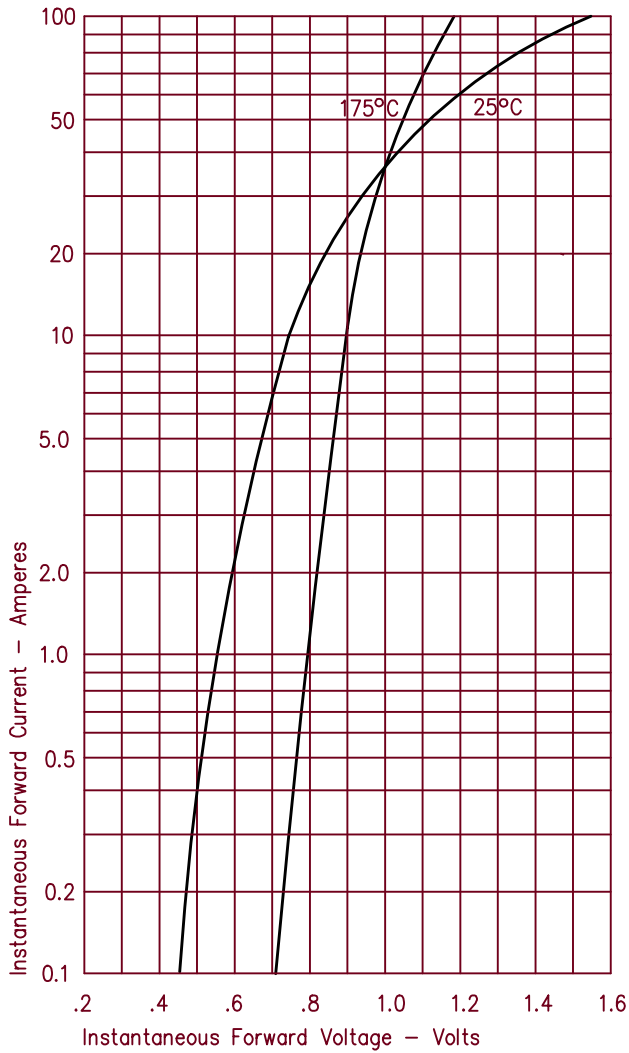


Figure 3  
Forward Current Derating

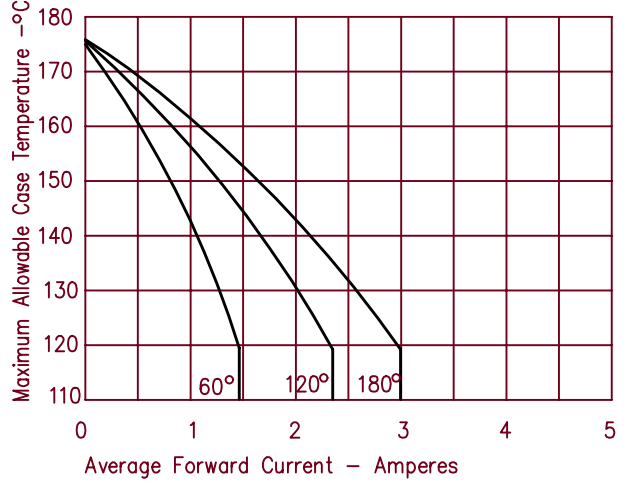


Figure 2  
Typical Reverse Characteristics

